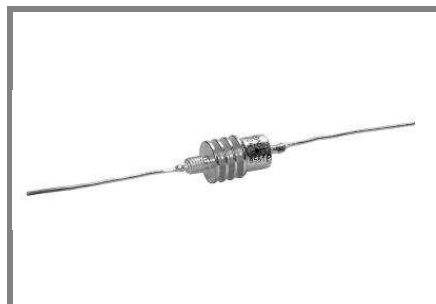




Stud Diode

Rectifier Diode

SKN 2,5

Features

- Reverse voltages up to 1600 V
- Hermetic metal case with glass insulator
- Anode side threaded stud ISO M4 (with lead wire in addition)
- SKN: anode to stud

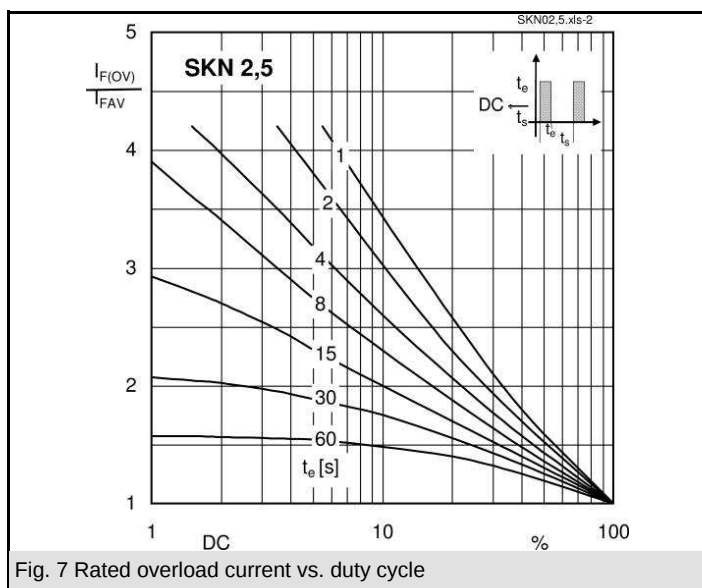
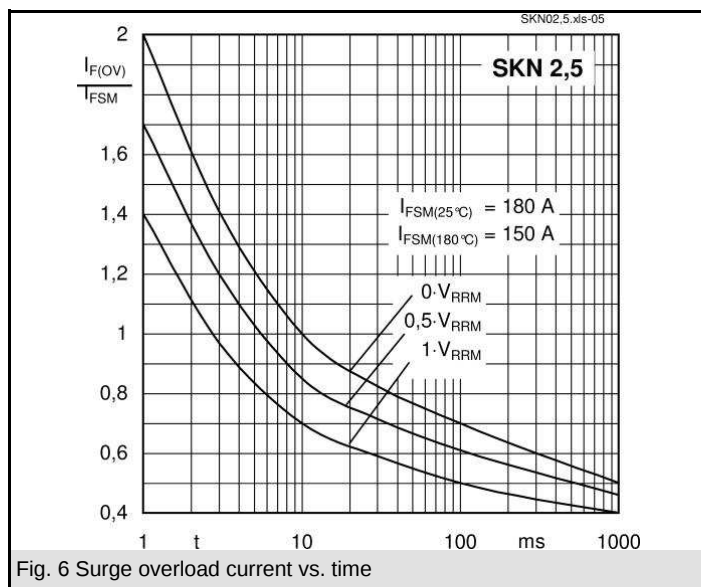
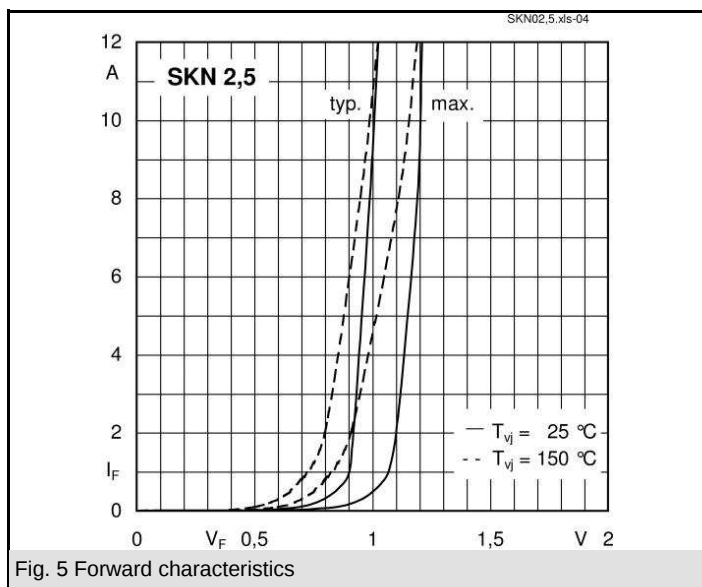
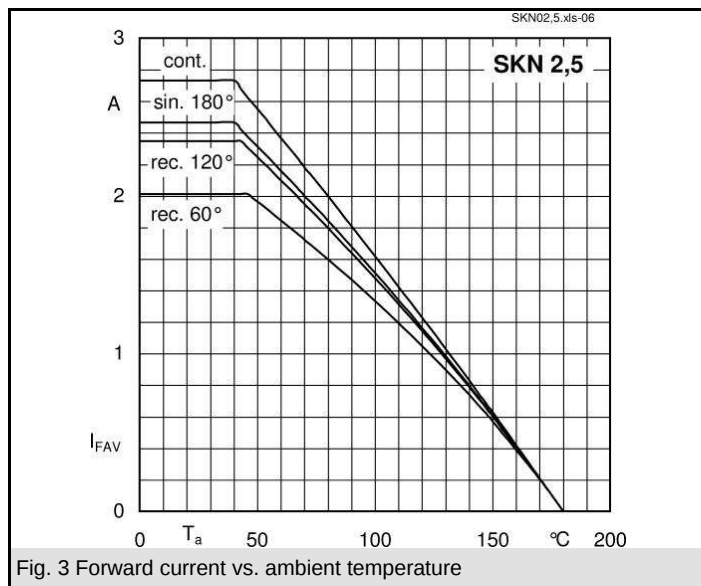
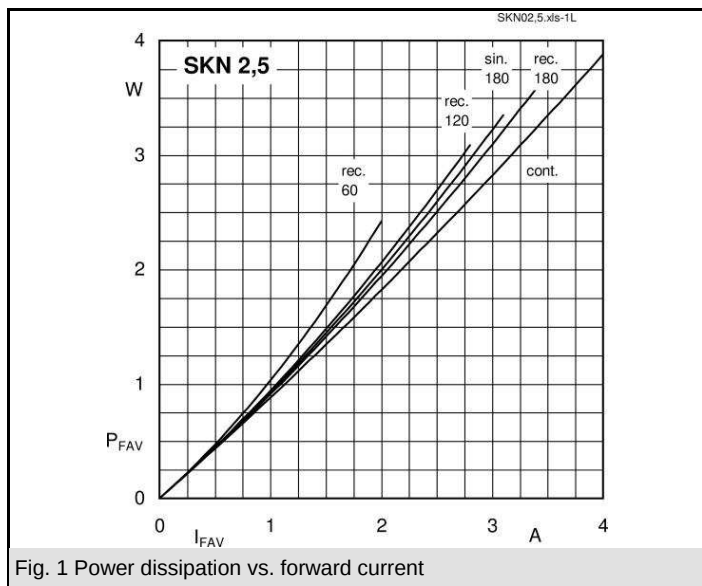
Typical Applications*

- All-purpose rectifier diodes
- For severe ambient conditions
- Recommended snubber network:
RC: 0,02 μ F, 500 Ω ($P_R = 1$ W)
 $R_P = 270$ k Ω ($P_R = 2$ W)

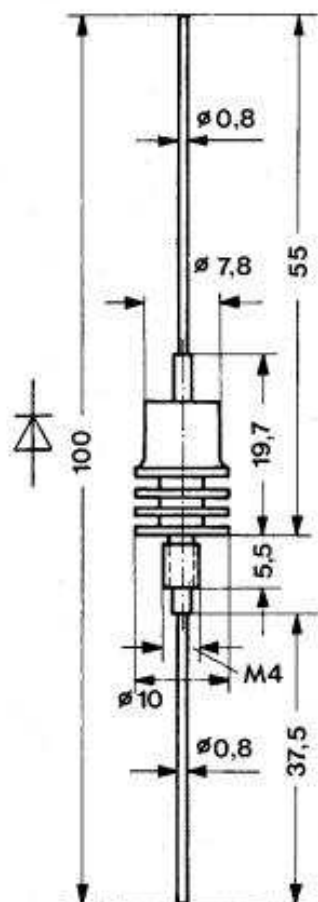
V_{RSM} V	V_{RRM} V	$I_{FRMS} = 5$ A (maximum value for continuous operation) $I_{FAV} = 2,5$ A (sin. 180; $T_a = 45$ °C)		
400	400	SKN 2,5/04		
800	800	SKN 2,5/08		
1200	1200	SKN 2,5/12		
1600	1600	SKN 2,5/16		

Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; $T_a = 45$ (85) °C	2,5 (1,8)	A
I_{FSM}	$T_{vj} = 25$ °C; 10 ms	180	A
	$T_{vj} = 180$ °C; 10 ms	150	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms	160	A ² s
	$T_{vj} = 180$ °C; 8,3 ... 10 ms	110	A ² s
V_F	$T_{vj} = 25$ °C; $I_F = 10$ A	max. 1,2	V
$V_{(TO)}$	$T_{vj} = 180$ °C	max. 0,85	V
r_T	$T_{vj} = 180$ °C	max. 30	m Ω
I_{RD}	$T_{vj} = 180$ °C; $V_{RD} = V_{RRM}$	max. 1,5	mA
Q_{rr}	$T_{vj} = 160$ °C; $-di_F/dt = 10$ A/ μ s	15	μ C
$R_{th(j-c)}$		2,5	K/W
$R_{th(j-a)}$		55	K/W
T_{vj}		- 40 ... + 180	°C
T_{stg}		- 55 ... + 180	°C
V_{isol}		-	V~
M_s	to heatsink	0,8	Nm
a		5 * 9,81	m/s ²
m	approx.	6	g
Case		E 5	





Dimensions in mm



Case E 5 (IEC 60191: A 2 modified; JEDEC: DO-1 modified)

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.